

2SC5839

Silicon NPN epitaxial planar type

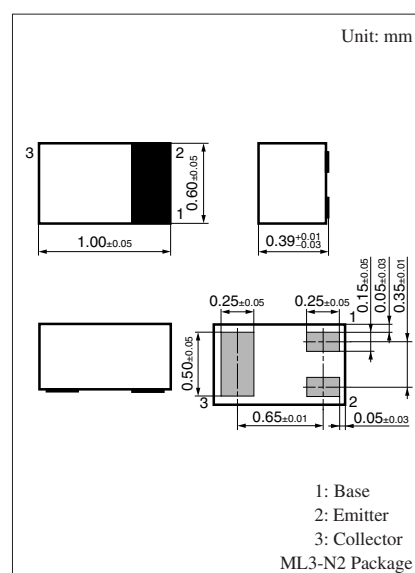
For low-voltage high-frequency amplification

■ Features

- High transition frequency f_T
- Suitable for high-density mounting and downsizing of the equipment for Ultraminiature leadless package
0.6 mm × 1.0 mm (height 0.39 mm)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|-----------|-------------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | 9 | V |
| Collector-emitter voltage (Base open) | V_{CEO} | 6 | V |
| Emitter-base voltage (Collector open) | V_{EBO} | 2 | V |
| Collector current | I_C | 30 | mA |
| Collector power dissipation | P_C | 100 | mW |
| Junction temperature | T_j | 125 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +125 | $^\circ\text{C}$ |

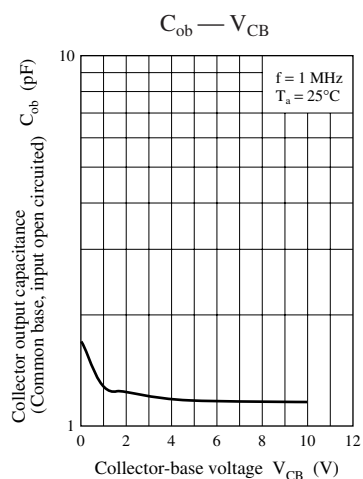
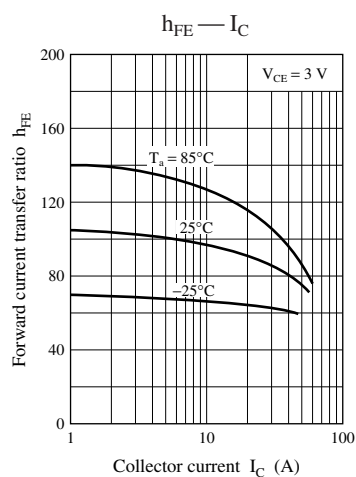
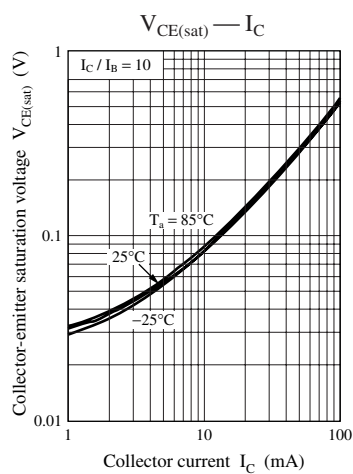
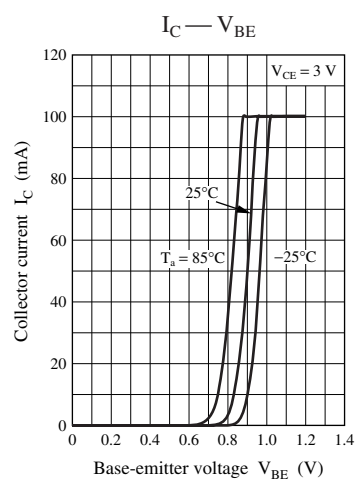
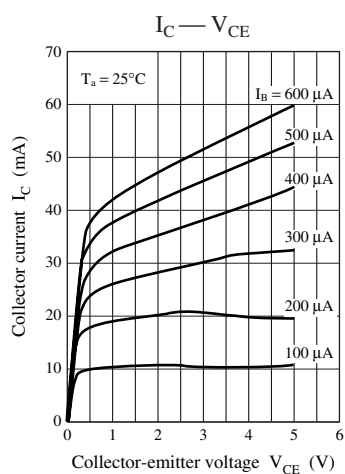
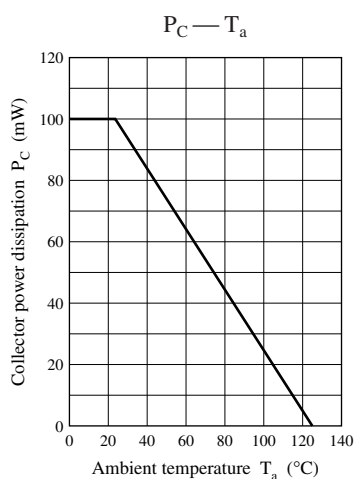


Marking Symbol: 1N

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|---|---------------|--|-----|-----|-----|---------------|
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 5\text{ V}, I_E = 0$ | | | 1 | μA |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{EB} = 1\text{ V}, I_C = 0$ | | | 1 | μA |
| Forward current transfer ratio | h_{FE} | $V_{CE} = 3\text{ V}, I_C = 10\text{ mA}$ | 40 | 100 | 160 | — |
| Transition frequency | f_T | $V_{CE} = 3\text{ V}, I_C = 10\text{ mA}, f = 1.5\text{ GHz}$ | | 10 | | GHz |
| Forward transfer gain | $ S_{21e} ^2$ | $V_{CE} = 0.3\text{ V}, I_C = 1\text{ mA}, f = 0.9\text{ GHz}$ | | 6.5 | | dB |
| Noise figure | NF | $V_{CE} = 0.3\text{ V}, I_C = 1\text{ mA}, f = 0.9\text{ GHz}$ | | 1.7 | | dB |
| Collector output capacitance (Common base, input open circuited) | C_{ob} | $V_{CB} = 3\text{ V}, I_E = 0, f = 1\text{ MHz}$ | | 0.4 | 0.7 | pF |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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